

Amendments to the Claims:

This listing of the claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

Claim 1 (cancelled)

Claim 2 (previously presented): A semiconductor device, comprising:
a semiconductor substrate;
a first insulating film formed on said semiconductor substrate;
a polysilicon resistor film formed on said first insulating film;
a second insulating film formed on said resistor film;
a pair of terminal wirings formed on said second insulating film and connected to said resistor film; and

a high heat conductor film consisting of a highly heat-conducting material formed on said second insulating film, said high heat conductor film formed in a predetermined area including an area above said resistor film between said pair of terminal wirings,

wherein a thickness of said high heat conductor film is thicker than a thickness of said resistor film, and said high heat conductor film is spaced apart from at least one of said pair of terminal wirings.

Claim 3 (original): The semiconductor device according to claim 2 wherein the thickness of said high heat conductor film is twice the thickness of said resistor film or thicker.

Claim 4 (currently amended): The A semiconductor device, comprising:

a semiconductor substrate;

a first insulating film formed on said semiconductor substrate;
a polysilicon resistor film formed on said first insulating film;
a second insulating film formed on said resistor film;
a high heat conductor film of a highly heat-conducting material formed on said second insulating film,

a pair of terminal wirings formed on said second insulating film and connected to said resistor film,

wherein a thickness of said high heat conductor film is greater than a thickness of said resistor film, and a width of said high heat conductor film is greater than a width of said resistor film and said high heat conductor film is formed in a predetermined area including an area above said resistor film between said pair of terminal wirings.

Claim 5 (original): The semiconductor device according to claim 2, wherein said high heat conductor film is united with one of said terminal wirings.

Claim 6 (previously presented): A semiconductor device, comprising:

a semiconductor substrate;
a first insulating film formed on said semiconductor substrate;
a polysilicon resistor film formed on said first insulating film;
a second insulating film formed on said resistor film;
a pair of terminal wirings formed on said second insulating film and connected to said resistor film; and

a high heat conductor film consisting of a highly heat-conducting material formed on said second insulating film, said high heat conductor film formed in a predetermined area including an area above said resistor film between said pair of terminal wirings,

wherein a thickness of said second insulating film is thinner than a thickness of said resistor film, a thickness of said high heat conductor film is thicker than a thickness of said resistor film, and said high heat conductor film is spaced apart from at least one of said pair of terminal wirings.